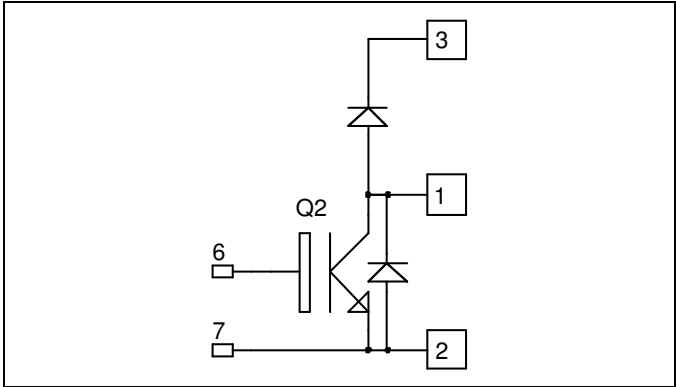


***Boost chopper
Trench IGBT® Power Module***

**$V_{CES} = 1200V$
 $I_C = 200A @ T_c = 80^\circ C$**

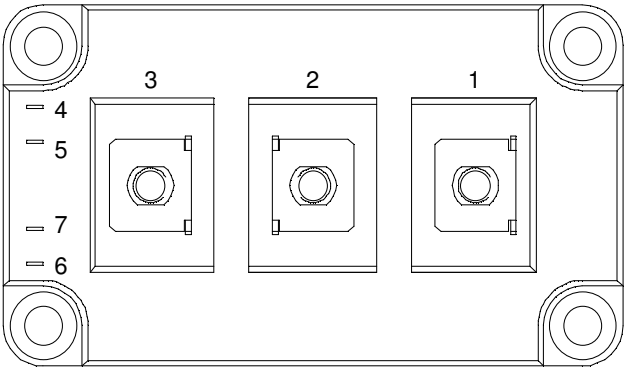


Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
 - M6 power connectors
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat

Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>		<i>Max ratings</i>	<i>Unit</i>
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	300	A
		$T_C = 80^\circ C$	200	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	400	
V_{GE}	Gate - Emitter Voltage		± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	1040	W
SCSOA	Short Circuit Safe Operating Area	$T_j = 125^\circ C$	800A@900V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 6mA$	1200			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			6	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 200A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.4 2.0	2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 6mA$	5.0	5.8	6.5	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		14		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.8		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		0.66		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		280		ns
T_r	Rise Time	$V_{GE} = \pm 15V$		90		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 200A$		550		
T_f	Fall Time	$R_G = 3.6\Omega$		130		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		300		ns
T_r	Rise Time	$V_{GE} = \pm 15V$		100		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 200A$		650		
T_f	Fall Time	$R_G = 3.6\Omega$		180		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 200A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.6 1.6	2.1	V
E_{rec}	Reverse Recovery Energy	$I_F = 200A$ $V_R = 600V$ $di/dt = 900A/\mu s$	$T_j = 125^\circ\text{C}$	17		mJ
Q_{rr}	Reverse Recovery Charge	$I_F = 200A$ $V_R = 600V$ $di/dt = 900A/\mu s$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	20 36		μC

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case	IGBT Diode		0.12 0.20	$^\circ\text{C/W}$	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1$ min, $I_{isol} < 1mA, 50/60Hz$	2500			V	
T_j	Operating junction temperature range	-40		150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		125		
Torque	Mounting torque	For terminals To Heatsink	M6 M6	3 3	5 5	N.m
Wt	Package Weight			380	g	

